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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :
YASUJI HIRAMATSU ET AL : ATTN: APPLICATION DIVISION
SERIAL NO: 10/069,510 :
FILED: March 4, 2002 :
FOR: HOT PLATE FOR SEMICONDUCTOR
PRODUCING/EXAMINING DEVICE

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to a first examination on the merits, please amend the above-identified
application as follows:

IN THE TITLE

Please delete the current title and insert therefor:

HOT PLATE FOR SEMICONDUCTOR MANUFACTURE AND TESTING

IN THE CLAIMSPlease amend Claims 3 and 4 to read as follows:¹

¹A marked-up copy of the amendments is attached hereto.

3. (Amended) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein said ceramic substrate is subjected to an annealing treatment.

4. (Amended) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

Please add new claims 5-8 as follows:

5. The hot plate for a semiconductor producing/examining device according to claim 2,

wherein said ceramic substrate is subjected to an annealing treatment.

6. (New) The hot plate for a semiconductor producing/examining device according to claim 2,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

7. (New) The hot plate for a semiconductor producing/examining device according to claim 3,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

8. (New) The hot plate for a semiconductor producing/examining device according to claim 5,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

IN THE ABSTRACT

Please amend the Abstract on page 49 to read as follows:²

ABSTRACT

A hot plate for a semiconductor producing/examining device, in which hot plate, when an object to be heated such as a silicon wafer is heated in a state that the object is distanced by a certain distance from the heating face, air is less likely to stagnate between the silicon wafer and the heating face and thus the object to be heated can be evenly heated. Specifically, the hot plate for a semiconductor producing/examining device includes a resistance heating element formed on a surface of a ceramic substrate or inside the ceramic substrate, wherein the glossiness of the heating face of the ceramic substrate is 1.5% or more.

REMARKS

Favorable consideration of this application, as presently amended, is respectfully requested.

The present preliminary amendment is submitted to place the above-identified application in more proper format under United States practice.

By the present preliminary amendment the Title is amended to match that on the International publication.

²A marked-up copy of the amendment is attached hereto.

Claims 3 and 4 are amended by the present response to no longer recite any multiple dependencies. Further, subject matter of the canceled multiple dependencies is now set forth in new dependent claims 5-8.

The Abstract has also been amended by the present response to be in more proper format under United States practice.

The present application is believed to be in condition for a full and thorough examination on the merits. An early and favorable consideration of the present application is hereby respectfully requested.

Respectfully submitted,

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Amendment Filed on:

6-20-2002IN THE TITLE

--[HOT PLATE FOR SEMICONDUCTOR PRODUCING/EXAMINING DEVICE]

HOT PLATE FOR SEMICONDUCTOR MANUFACTURE AND TESTINGIN THE CLAIMS

3. (Amended) The hot plate for a semiconductor producing/examining device according to claim 1 [or 2],

wherein said ceramic substrate is subjected to an annealing treatment.

4. (Amended) The hot plate for a semiconductor producing/examining device according to [any of claims 1 to 3] claim 1,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

Claims 5-8 (New).--

IN THE ABSTRACT

ABSTRACT

[An object of the present invention is to provide a] A hot plate for a semiconductor producing/examining device, in which hot plate, when an object to be heated such as a silicon wafer is heated in a state that the object is distanced by a certain distance from the heating

face, air is less likely to stagnate between the silicon wafer and the heating face and thus the object to be heated can be evenly heated. Specifically, the hot plate for a semiconductor producing/examining device [of the present invention comprises] includes a resistance heating element formed on a surface of a ceramic substrate or inside the ceramic substrate, wherein the glossiness of the heating face of [said] the ceramic substrate is 1.5% or more.--